



# GaN-HEMT 30W

# EGN35C030MK

High Voltage - High Power GaN-HEMT

### FEATURES

- High Voltage Operation :  $V_{DS}=50V$
- High Power : 45.0dBm (typ.) @  $P_{sat}$
- Power Gain : 16.5dB(typ.) @  $f=3.5GHz$
- Proven Reliability

### DESCRIPTION

SEDI's GaN-HEMT offers high efficiency, ease of matching, greater consistency and broad bandwidth for high power L-band amplifiers with 50V operation, and gives you higher gain.

This new product is ideally suited for use in 3.5GHz WiMAX design requirements as it offers high gain, long term reliability and ease of use.



### ABSOLUTE MAXIMUM RATINGS (Case Temperature $T_c=25^{\circ}C$ )

Item	Symbol	Condition	Rating	Unit
Operating-Voltage	$V_{DS}$		55	V
Drain-Source Voltage	$V_{DS}$	$V_{GS}=-8V$	160	V
Gate-Source Voltage	$V_{GS}$		-15	V
Total Power Dissipation	$P_t$		37.5	W
Storage Temperature	$T_{stg}$		-65 to +175	$^{\circ}C$
Channel Temperature	$T_{ch}$		250	$^{\circ}C$

### RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
DC Input Voltage	$V_{DS}$		$\leq 55$	V
Forward Gate Current	$I_{GF}$	$R_G=15\Omega$	$\leq 69$	mA
Reverse Gate Current	$I_{GR}$	$R_G=15\Omega$	$\geq -1.1$	mA
Channel Temperature	$T_{ch}$		$\leq 180$	$^{\circ}C$
Average Output Power	$P_{ave.}$		$\leq 42.0$	dBm

### ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25^{\circ}C$ )

Item	Symbol	Condition	Limit			Unit
			min.	Typ.	Max.	
Pinch-Off Voltage	$V_p$	$V_{DS}=50V$ $I_{DS}=7.8mA$	-1.0	-1.5	-2.0	V
Saturated Power	$P_{sat} *1$	$V_{DS}=50V$	44.0	45.0	-	dBm
Drain Efficiency	$\eta_d *2$	$I_{DS}(DC)=150mA$	9	11	-	%
Power Gain	$G_p *2$	$f=3.50GHz$	15.5	16.5	-	dB
Thermal Resistance	$R_{th}$	Channel to Case at 24W $P_{DC}$	-	5.0	6.0	$^{\circ}C/W$

\*1 : 10%-duty RF pulse (DC supply constant)

\*2 :  $P_{out} = 31.5dBm$ , CW



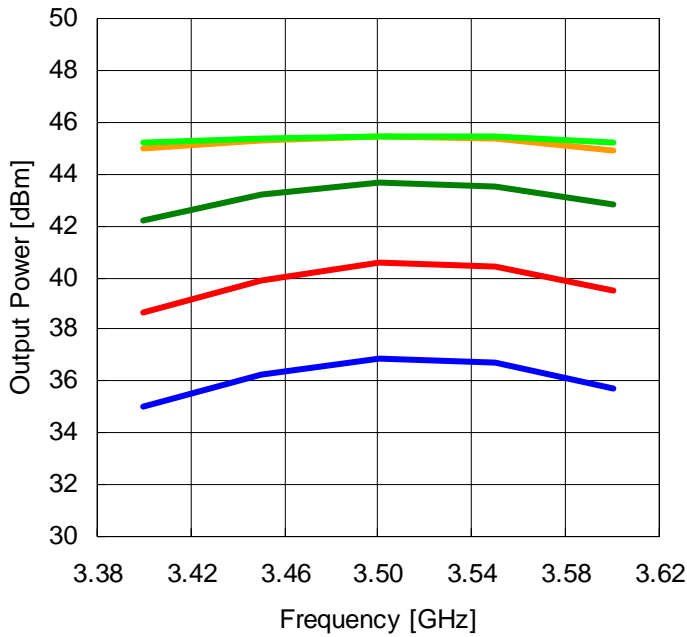
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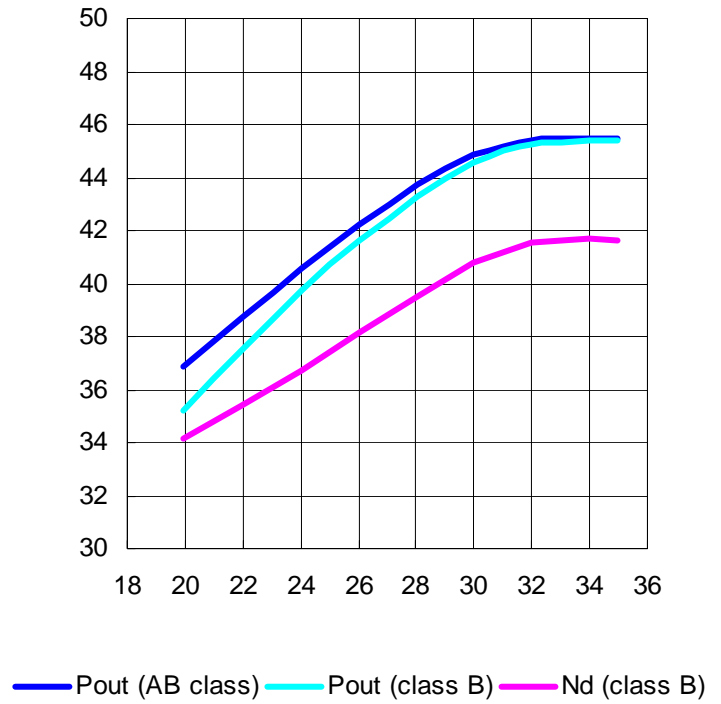
RF characteristics @f=3.5GHz fine tuned

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Output Power vs. Frequency  
V<sub>DS</sub>=50V, I<sub>DS(DC)</sub>=150mA

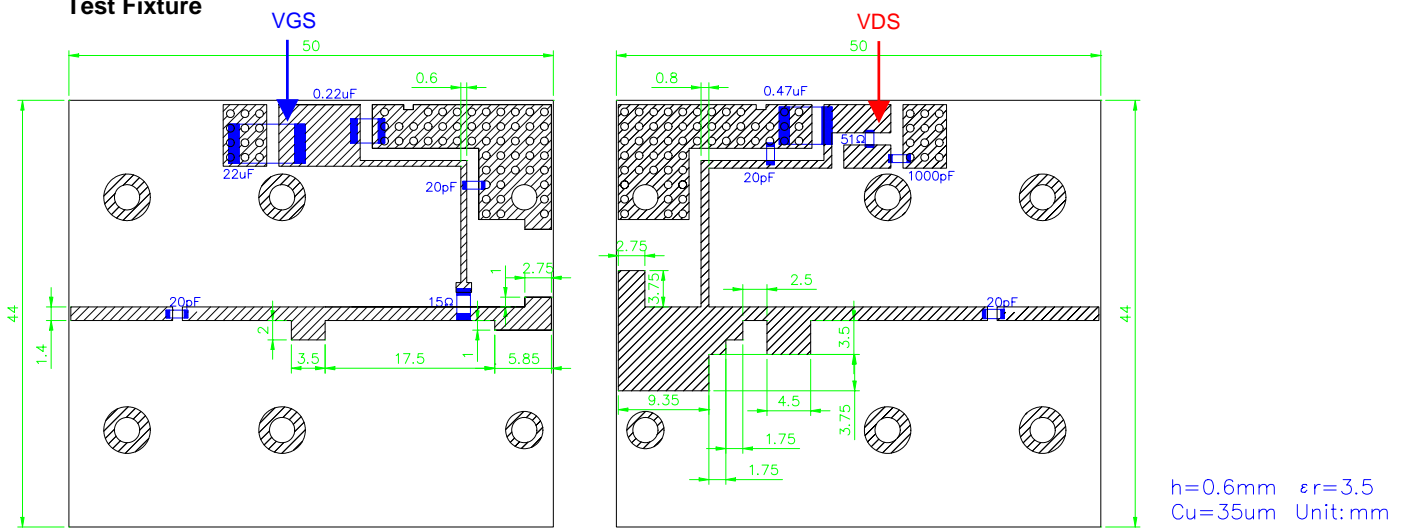


Output Power and Drain Efficiency vs. Input Power  
V<sub>DS</sub>=50V, I<sub>DS(DC)</sub>=150mA, f=3.50GHz



Pulse Signal (10%-duty, DC : constant)

Test Fixture



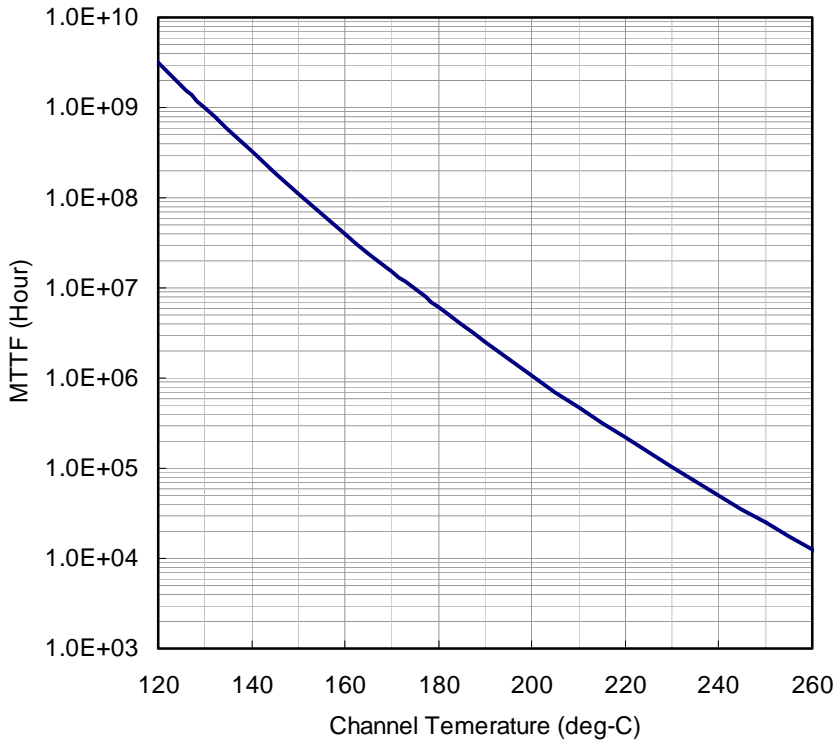


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MTTF Calculation  
- Estimated MTTF -



Ea=1.6eV  
Confidence Level=90%

Channel Temp (deg-C)	MTTF (Hours)
160	4.05 x 10 <sup>7</sup>
180	6.07 x 10 <sup>6</sup>
200	1.07 x 10 <sup>6</sup>

$$AF = \exp\left[-\frac{Ea}{k}\left(\frac{1}{T_{stress}} - \frac{1}{T_{use}}\right)\right]$$

$$MTTF_{use} = MTTF_{stress} * AF$$

Where;

AF: acceleration factor

Ea: activation energy (1.6 eV)

k: Boltzman's constant (8.62 x 10<sup>-5</sup> eV/K)

T<sub>stress</sub>: stress temperature (K)

T<sub>use</sub>: use temperature (K)

### ESD characteristic

Test Methodology	Class
Human Body Model (per JESD22-A114)	0
Machine Model (per JEI/ESD22-A115)	A



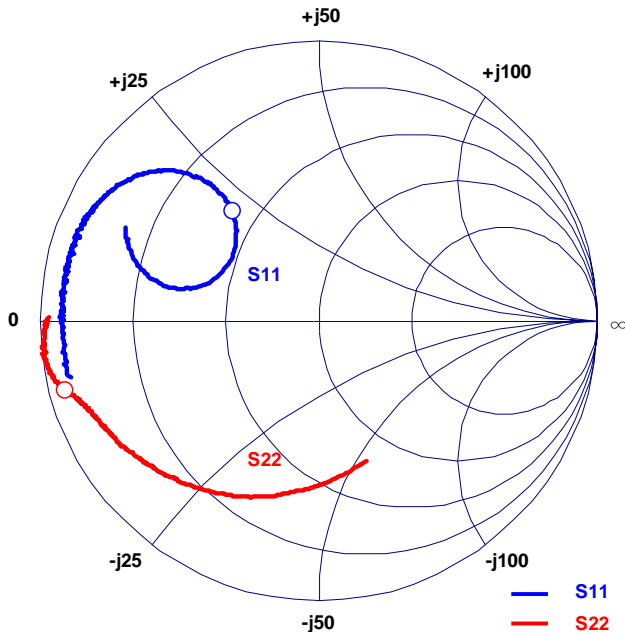
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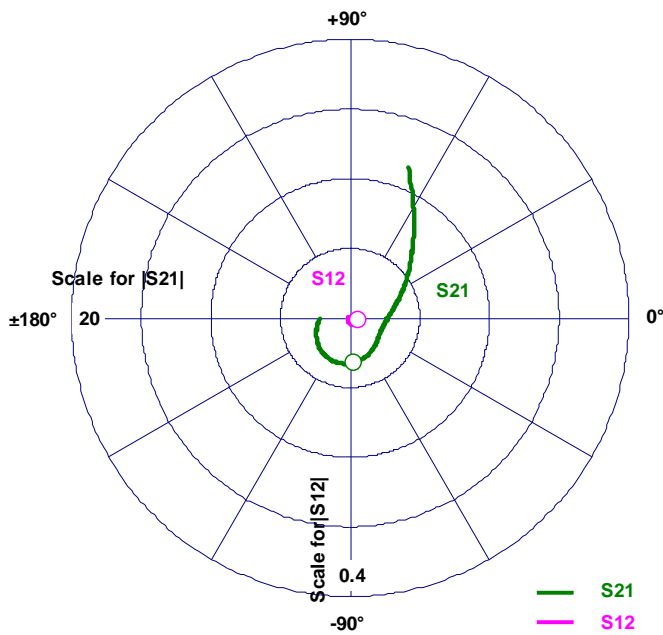
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- Reference DATA -

S-Parameters @V<sub>DS</sub>=50V, I<sub>DS(DC)</sub>=150mA, f=0.5 to 4.5GHz  
Z<sub>I</sub> = Z<sub>S</sub> = 50 ohm      Marker : 3.50GHz



Freq. GHz	S <sub>11</sub>		S <sub>21</sub>		S <sub>12</sub>		S <sub>22</sub>	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
0.50	0.91	-167.14	11.61	68.89	0.008	-6.03	0.53	-71.18
0.60	0.92	-171.60	9.57	61.82	0.007	-9.26	0.55	-79.90
0.70	0.92	-175.48	8.03	55.27	0.007	-10.66	0.58	-87.59
0.80	0.92	-178.48	6.94	49.43	0.006	-15.34	0.60	-94.62
0.90	0.93	179.06	6.08	43.95	0.006	-13.78	0.63	-101.09
1.00	0.93	176.26	5.36	38.67	0.005	-18.00	0.65	-106.85
1.10	0.92	173.62	4.85	33.48	0.005	-14.38	0.68	-112.27
1.20	0.93	171.84	4.36	28.74	0.005	-16.58	0.70	-117.26
1.30	0.92	169.49	3.97	24.07	0.004	-12.14	0.72	-121.63
1.40	0.92	167.77	3.64	20.28	0.004	-6.47	0.74	-125.38
1.50	0.93	165.81	3.39	15.94	0.004	1.59	0.75	-129.24
1.60	0.92	164.45	3.16	11.67	0.004	5.47	0.77	-132.66
1.70	0.91	162.88	2.97	8.03	0.004	10.46	0.78	-135.94
1.80	0.91	161.08	2.83	4.37	0.004	10.89	0.79	-138.72
1.90	0.91	158.93	2.70	0.56	0.004	22.66	0.81	-141.31
2.00	0.92	157.55	2.59	-3.12	0.004	24.96	0.82	-143.70
2.10	0.91	155.70	2.53	-7.36	0.005	29.67	0.83	-145.62
2.20	0.91	154.01	2.47	-10.88	0.004	28.85	0.84	-147.70
2.30	0.90	152.08	2.42	-15.06	0.005	33.51	0.84	-149.88
2.40	0.89	150.19	2.40	-18.43	0.006	30.33	0.85	-151.97
2.50	0.88	148.17	2.39	-22.44	0.006	32.26	0.86	-153.36
2.60	0.87	146.19	2.40	-26.84	0.007	32.03	0.86	-154.78
2.70	0.85	143.82	2.43	-31.18	0.007	27.75	0.87	-156.43
2.80	0.83	141.42	2.48	-35.91	0.008	30.27	0.88	-157.56
2.90	0.81	139.07	2.54	-40.98	0.009	27.38	0.88	-158.62
3.00	0.78	136.35	2.63	-46.57	0.009	24.42	0.89	-159.89
3.10	0.74	133.70	2.73	-52.99	0.010	16.37	0.90	-161.16
3.20	0.70	131.34	2.85	-59.74	0.011	11.69	0.90	-161.94
3.30	0.64	128.79	2.98	-67.53	0.011	5.10	0.92	-162.63
3.40	0.57	127.71	3.11	-75.94	0.012	-0.22	0.93	-163.88
3.50	0.50	128.41	3.23	-85.76	0.013	-9.93	0.94	-164.79
3.60	0.43	133.72	3.31	-96.03	0.013	-23.25	0.96	-166.05
3.70	0.39	142.80	3.33	-106.86	0.012	-32.19	0.97	-167.37
3.80	0.39	155.13	3.27	-118.49	0.011	-46.00	0.98	-169.22
3.90	0.44	163.56	3.16	-129.43	0.010	-61.37	0.99	-171.01
4.00	0.51	167.26	3.02	-140.07	0.008	-73.73	0.99	-172.70
4.10	0.58	166.67	2.80	-149.74	0.007	-90.41	0.99	-174.73
4.20	0.65	164.91	2.63	-158.13	0.006	-120.14	0.99	-176.13
4.30	0.70	161.90	2.45	-166.16	0.005	-136.89	0.99	-177.84
4.40	0.74	158.14	2.29	-173.45	0.004	-165.04	0.98	-179.35
4.50	0.77	154.26	2.16	-179.91	0.004	171.95	0.97	179.16





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## MK Package Outline Metal-Ceramic Hermetic Package

